

LL24BT1006D

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LL24BT1006D

30W Ultra Low Capacitance Bi-Directional TVS For ESD Protection 24V

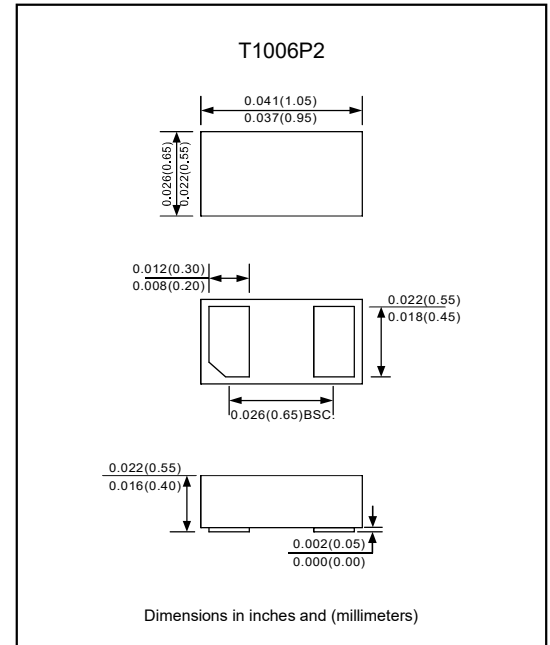
Features

- Array of surge rated diodes with internal TVS diode.
- Protects I/O lines.
- Each I/O pin can withstand over 1000 ESD strikes for $\pm 8\text{kV}$ contact discharge.
- Transient protection for high-speed data lines:
IEC 61000-4-2 (ESD) $\pm 10\text{kV}$ (Air), $\pm 10\text{kV}$ (Contact).
IEC 61000-4-5 (Lightning) 6A (8/20 μs).
Cable discharge event (CDE).
- Lead-free parts meet RoHS requirements.
- Suffix "-H" indicates Halogen-free parts, ex.LL24BT1006D-H.

Mechanical data

- Epoxy: UL94V-0 rated flame retardant.
- Case : Molded plastic, T1006P2.

Package outline



Maximum ratings (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Ratings	Units
Peak pulse current (8/20 μs)	I_{PP}	6	A
Peak pulse power (8/20 μs)	P_{PK}	30	W
ESD per IEC 61000-4-2 (Contact)	V_{ESD}	± 10	KV
ESD per IEC 61000-4-2 (Air)		± 10	
Charged device model	CDM	± 1000	V
Machine model	MM	± 200	V
Operating temperature	T_J	+125	$^\circ\text{C}$
Storage temperature range	T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical characteristics (At $T_A = 25^\circ\text{C}$ unless otherwise noted)

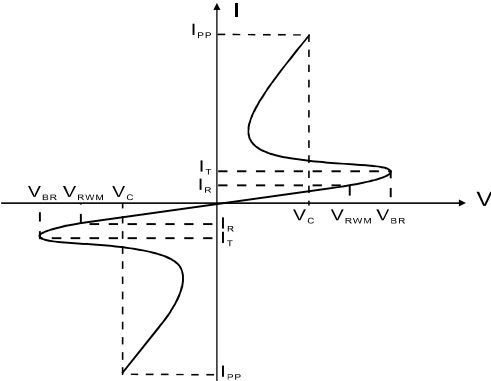
Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Reverse stand-off voltage		V_{RWM}			24	V
Reverse leakage current	$V_{RWM} = 24\text{V}$, $T = 25^\circ\text{C}$	I_R			1	μA
Breakdown voltage	$I_T = 100\mu\text{A}$	V_{BR}	25	26		V
Clamping voltage	$I_{PP} = 6\text{A}$, $t_p = 8/20\mu\text{s}$	V_C		5.5		V
Clamping voltage	$I_{PP} = 8\text{A}$, $t_p = 100\text{ns}$ (note1)	V_C		5		V
	$I_{PP} = 16\text{A}$, $t_p = 100\text{ns}$ (note1)			7.3		
Dynamic resistance	$I_{PP} = 12\text{A}$, $t_p = 100\text{ns}$ (note1)	R_{dyn}		0.29		Ω
Parasitic capacitance	$V_R = 0\text{V}$, $f = 1.0\text{MHz}$	C_{ESD}		0.2		pF

Note: 1. Measurements performed using a 100ns transmission line pulse (TLP) system.

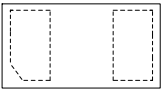
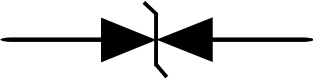
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Rating and characteristic curves

Symbol	Parameter
V_{RWM}	Nominal reverse working voltage
I_R	Reverse leakage current@ V_{RWM}
V_{BR}	Reverse breakdown voltage@ I_T
I_T	Test current for reverse breakdown
V_C	Clamping voltage @ I_{PP}
I_{PP}	Maximym peak pulse current
C_{ESD}	Parasitic capacitance



Pinning information

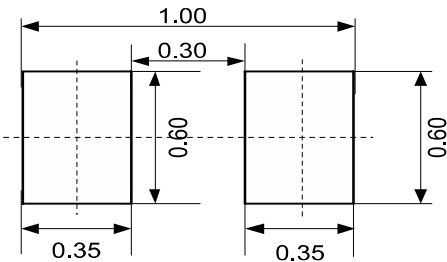
Pin	Simplified outline	Symbol
Bi-directional	 Top view  Bottom view	

Marking

Type number	Marking code
LL24BT1006D	MX

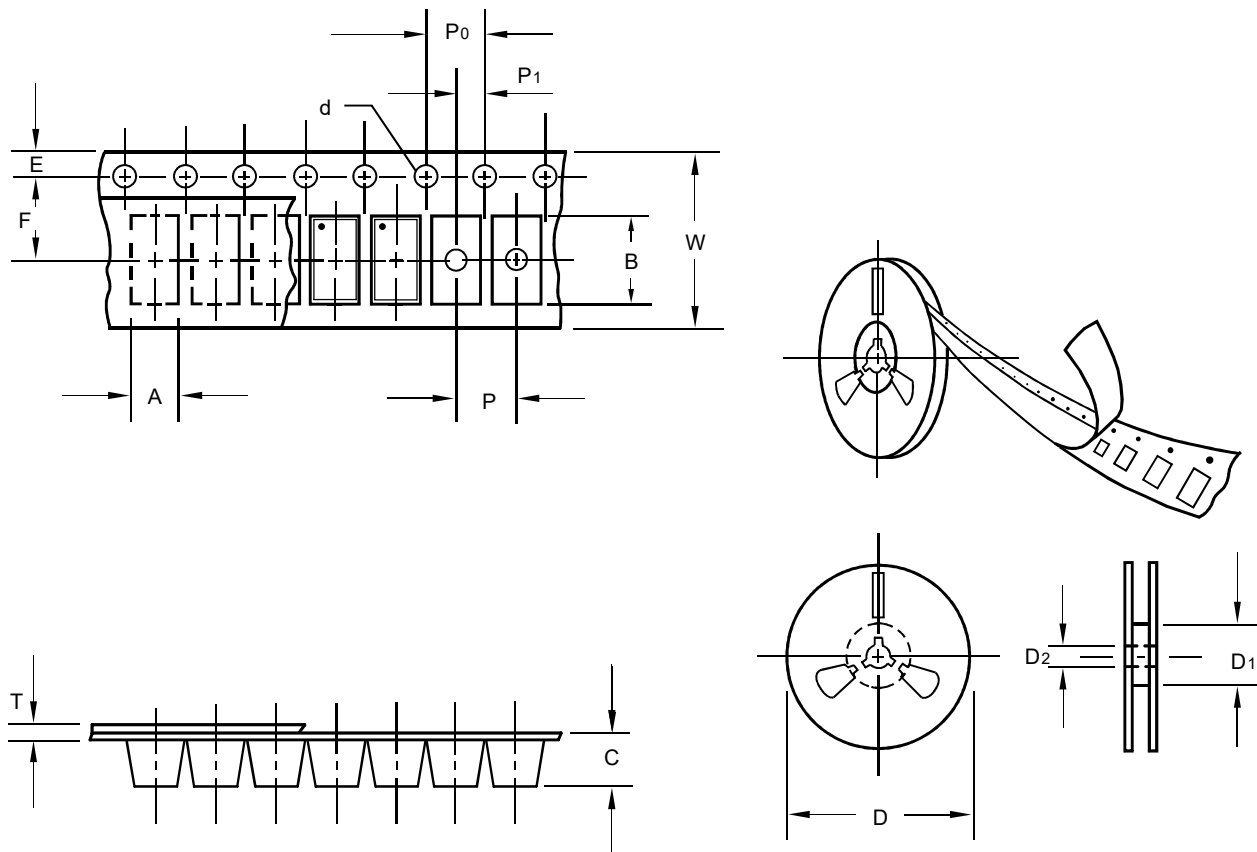
**"M" is part number.
"X" is the internal code.

Suggested solder pad layout



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Packing information



unit:mm

Item	Symbol	Tolerance	T1006P2
Carrier width	A	0.1	0.27
Carrier length	B	0.1	0.50
Carrier depth	C	0.1	0.17
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D ₁	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D ₁	min	55.00
Feed hole diameter	D ₂	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P ₀	0.1	4.00
Embossment center	P ₁	0.1	2.00
Overall tape thickness	T	0.1	0.20
Tape width	W	0.3	8.00

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

